HFZT

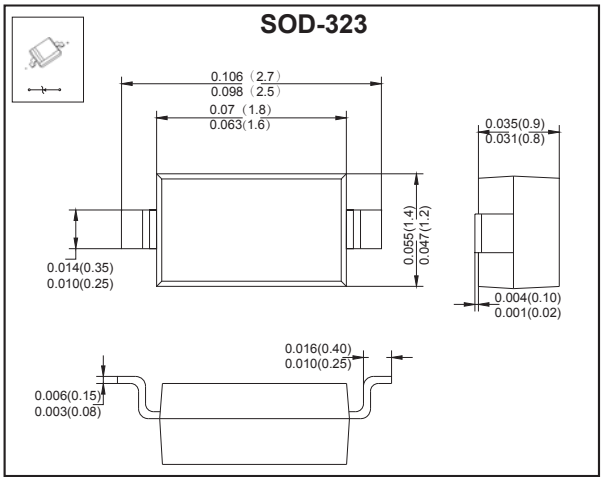
SD101BWS

Schottky Barrier Diode

VOLTAGE RANGE: 50V **PEAK PULSE POWER:200mW**

FEATURES

- Low Forward Voltage Drop
- Guard Ring Construction for Transient Protection
- Negligible Reverse Recovery Time
- Low Capacitance
- Ultra-small Surface Mount Package



MAXIMUM RATINGS AND CHARACTERISTICS

Ratings at 25 C ambient temperature unless otherwise specified

Symbol	Parameter	Value	Unit
V_{RRM}	Peak Repetitive Reverse Voltage	50	V
V_{RWM}	Working Peak Reverse Voltage		
V_R	DC Blocking Voltage		
$V_{R(RMS)}$	RMS Reverse Voltage	35	V
I_{FM}	Forward Continuous Current	15	mA
I_{FSM}	Non-repetitive Peak Forward Surge Current @t=8.3ms	2	A
P_D	Power Dissipation	200	mW
$R_{\Theta JA}$	Thermal Resistance from Junction to Ambient	500	℃/W
T_j	Junction Temperature	125	℃
T_{stg}	Storage Temperature	-55~+150	℃

Electrical Specification (T_A=25@25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Reverse voltage	$V_{(BR)}$	I_R=10μA	50			V
Reverse current	I_R	V_R=40V			0.2	μA
Forward voltage	V_F	I_F=1mA			0.40	V
		I_F=15mA			0.95	
Total capacitance	C_{tot}	V_R=0V,f=1MHz			2.1	pF
Reverse recovery time	t_{rr}	I_F= I_R=5mA, I_{rr}=0.1×I_R, R_L=100Ω			1	ns

MARKING: S2

RATINGS AND CHARACTERISTIC CURVES

Typical Characteristics